

# BCR3PM-12L

Triac

Low Power Use

REJ03G0301-0100

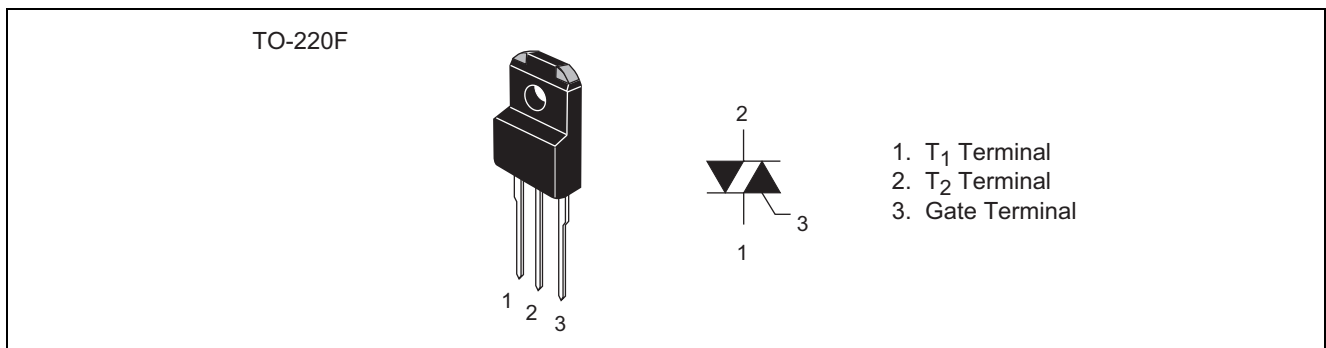
Rev.1.00

Aug.20.2004

## Features

- $I_{T(RMS)}$  : 3 A
- $V_{DRM}$  : 600 V
- $I_{FGTI}, I_{RGTI}, I_{RGTIII}$  : 20 mA (10 mA)<sup>Note5</sup>
- $V_{ISO}$  : 2000 V
- Insulated Type
- Planar Passivation Type
- UL Recognized : Yellow Card No. E223904  
File No. E80271

## Outline



## Applications

Contactless AC switch, light dimmer, electric blanket, control of household equipment such as electric fan, solenoid driver, small motor control, and other general purpose control applications

## Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak off-state voltage <sup>Note1</sup>	$V_{DRM}$	600	V
Non-repetitive peak off-state voltage <sup>Note1</sup>	$V_{DSM}$	720	V

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_T$ (RMS)	3.0	A	Commercial frequency, sine full wave 360° conduction, $T_c = 107^\circ\text{C}$
Surge on-state current	$I_{TSM}$	30	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
$I^2t$ for fusing	$I^2t$	3.7	$\text{A}^2\text{s}$	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	$P_{GM}$	3	W	
Average gate power dissipation	$P_{G(AV)}$	0.3	W	
Peak gate voltage	$V_{GM}$	6	V	
Peak gate current	$I_{GM}$	0.5	A	
Junction temperature	$T_j$	-40 to +125	$^\circ\text{C}$	
Storage temperature	$T_{stg}$	-40 to +125	$^\circ\text{C}$	
Mass	—	2.0	g	Typical value
Isolation voltage	Viso	2000	V	$T_a = 25^\circ\text{C}$ , AC 1 minute, $T_1\text{-}T_2\text{-}G$ terminal to case

Notes: 1. Gate open.

## Electrical Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak off-state current	$I_{DRM}$	—	—	2.0	mA	$T_j = 125^\circ\text{C}$ , $V_{DRM}$ applied
On-state voltage	$V_{TM}$	—	—	1.5	V	$T_c = 25^\circ\text{C}$ , $I_{TM} = 4.5\text{ A}$ , Instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	I	$V_{FGTI}$	—	—	1.5	$T_j = 25^\circ\text{C}$ , $V_D = 6\text{ V}$ , $R_L = 6\ \Omega$ , $R_G = 330\ \Omega$
	II	$V_{RGTI}$	—	—	1.5	
	III	$V_{RGTIII}$	—	—	1.5	
Gate trigger current <sup>Note2</sup>	I	$I_{FGTI}$	—	—	20 <sup>Note5</sup>	$T_j = 25^\circ\text{C}$ , $V_D = 6\text{ V}$ , $R_L = 6\ \Omega$ , $R_G = 330\ \Omega$
	II	$I_{RGTI}$	—	—	20 <sup>Note5</sup>	
	III	$I_{RGTIII}$	—	—	20 <sup>Note5</sup>	
Gate non-trigger voltage	$V_{GD}$	0.2	—	—	V	$T_j = 125^\circ\text{C}$ , $V_D = 1/2 V_{DRM}$
Thermal resistance	$R_{th(j-c)}$	—	—	4.5	$^\circ\text{C}/\text{W}$	Junction to case <sup>Note3</sup>
Critical-rate of rise of off-state commutating voltage <sup>Note4</sup>	$(dv/dt)_c$	5	—	—	$\text{V}/\mu\text{s}$	$T_j = 125^\circ\text{C}$

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

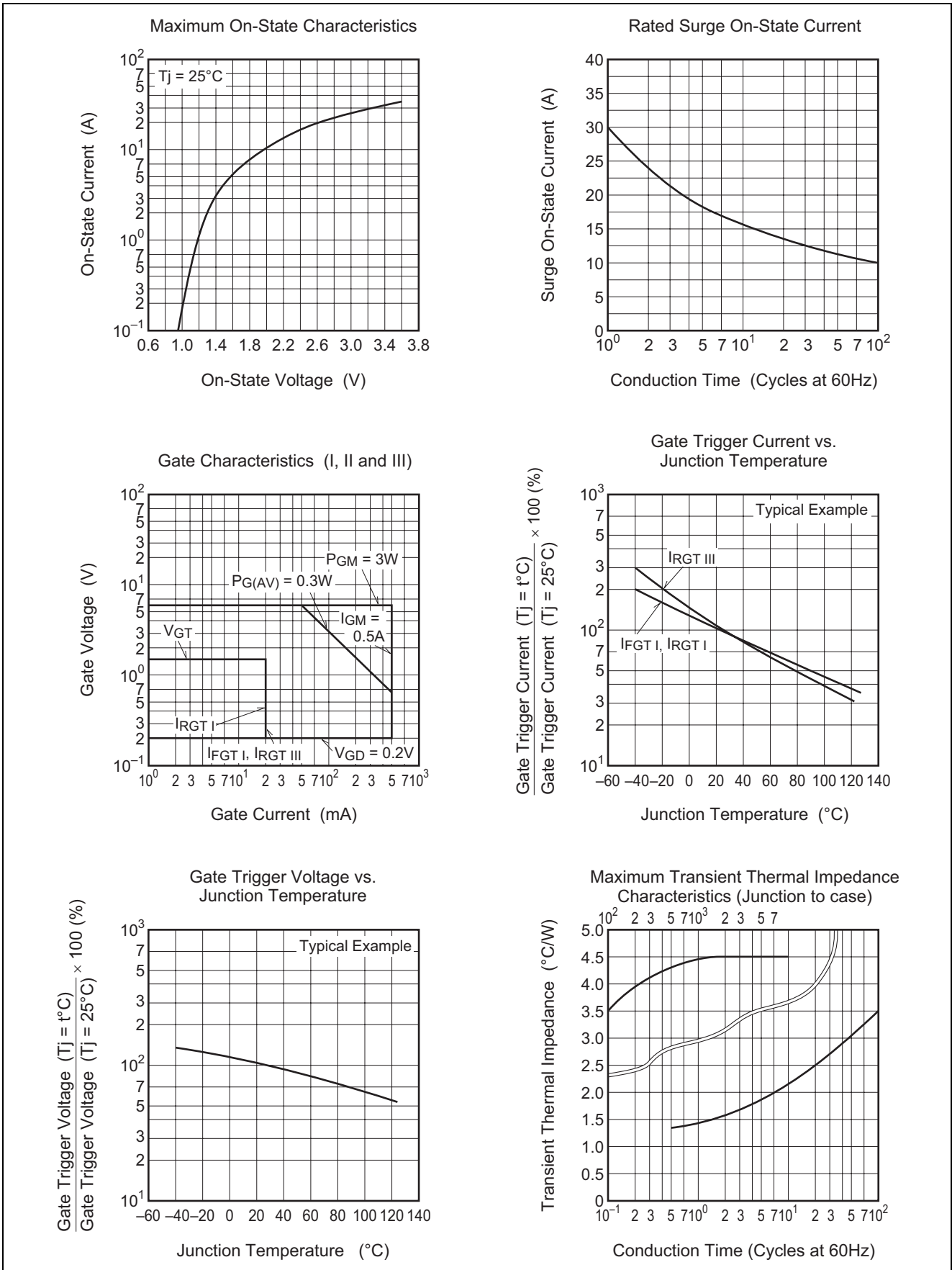
3. The contact thermal resistance  $R_{th(c-f)}$  in case of greasing is  $0.5^\circ\text{C}/\text{W}$ .

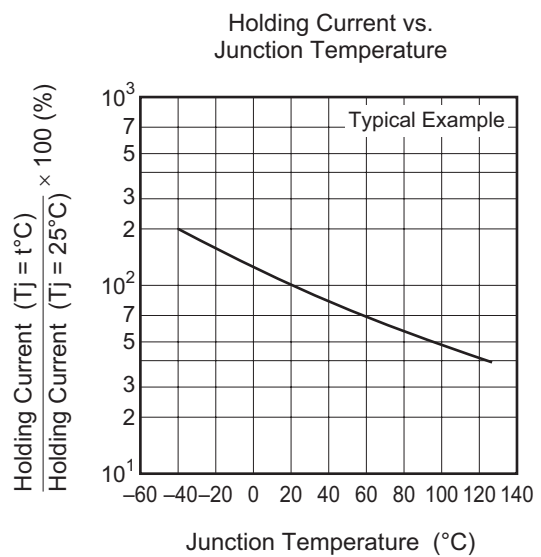
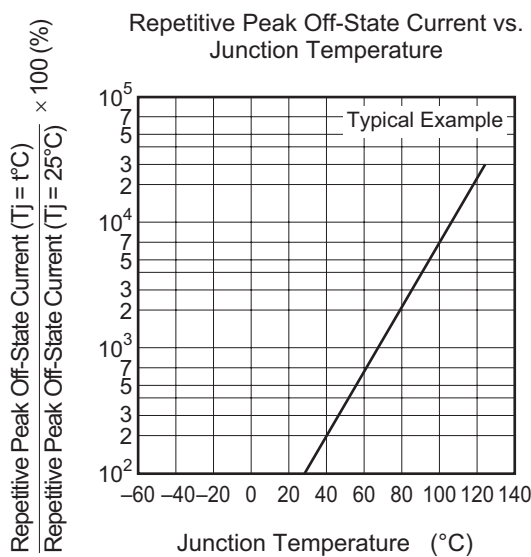
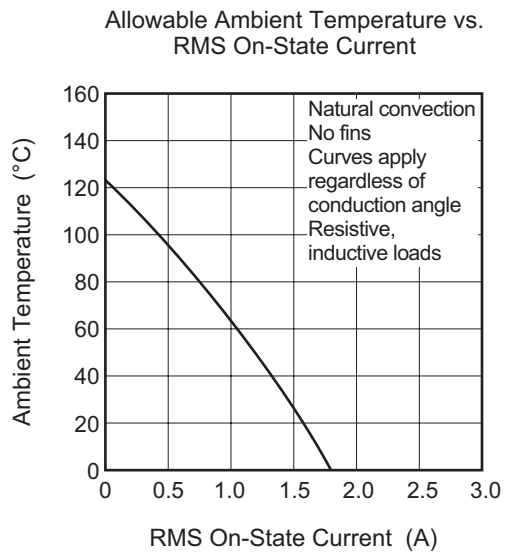
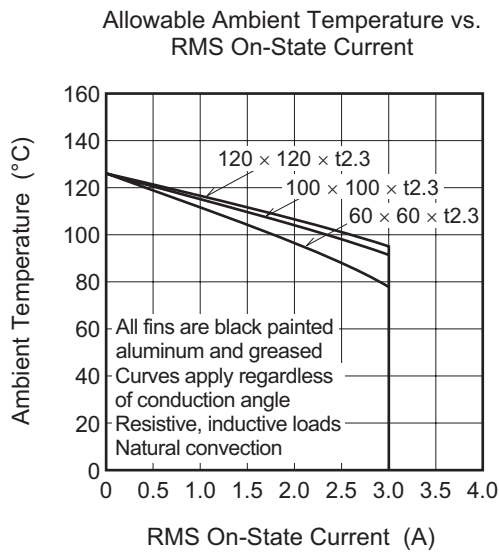
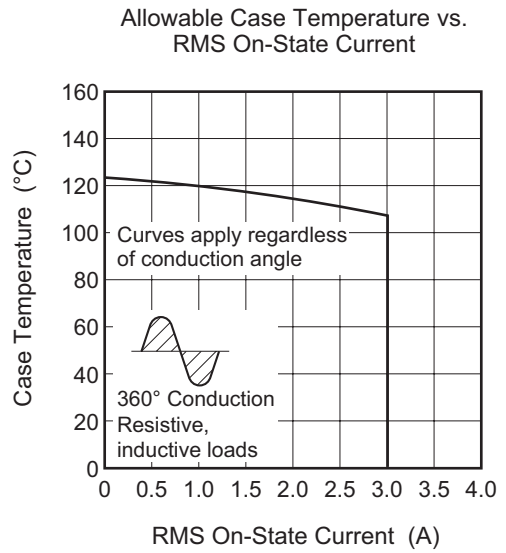
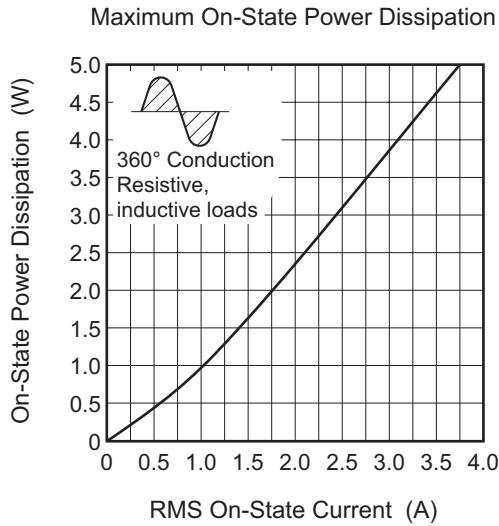
4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

5. High sensitivity ( $I_{GT} \leq 10\text{ mA}$ ) is also available. ( $I_{GT}$  item: 1)

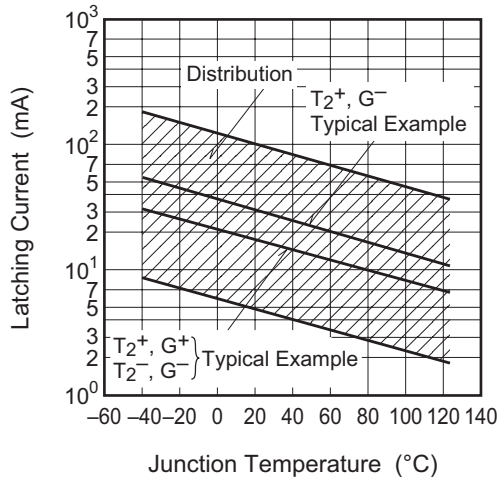
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature $T_j = 125^\circ\text{C}$ 2. Rate of decay of on-state commutating current $(di/dt)_c = -1.5\text{ A/ms}$ 3. Peak off-state voltage $V_D = 400\text{ V}$	

Performance Curves

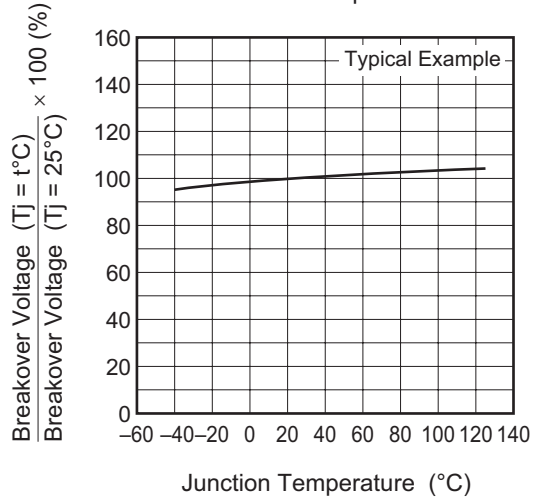




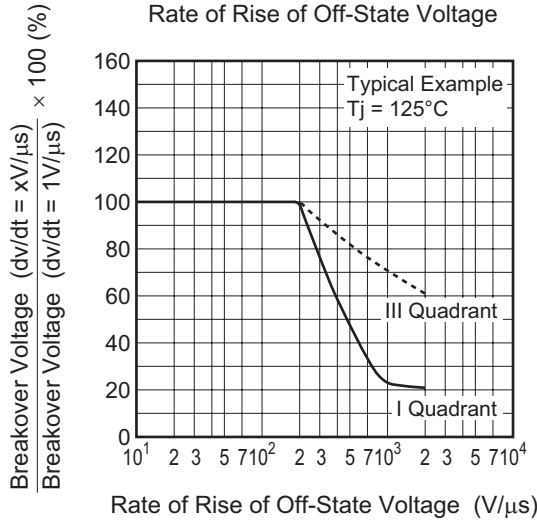
Latching Current vs. Junction Temperature



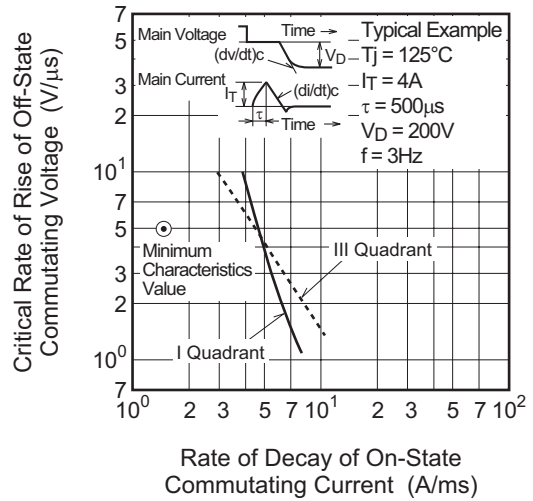
Breakover Voltage vs. Junction Temperature



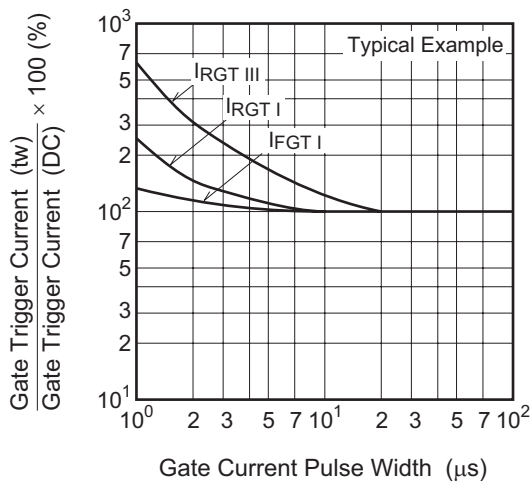
Breakover Voltage vs. Rate of Rise of Off-State Voltage



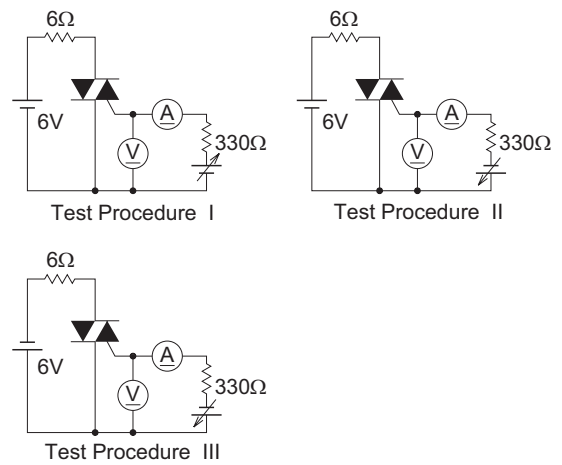
Commutation Characteristics



Gate Trigger Current vs. Gate Current Pulse Width



Gate Trigger Characteristics Test Circuits



### Package Dimensions

**TO-220F**

EIAJ Package Code	JEDEC Code	Mass (g) (reference value)	Lead Material
Conforms	—	2.0	Cu alloy

Note 1) The dimensional figures indicate representative values unless otherwise the tolerance is specified.

Symbol	Dimension in Millimeters		
	Min	Typ	Max
A	—	—	—
A <sub>1</sub>	—	—	—
A <sub>2</sub>	—	—	—
b	—	—	—
D	—	—	—
E	—	—	—
e	—	—	—
x	—	—	—
y	—	—	—
y <sub>1</sub>	—	—	—
ZD	—	—	—
ZE	—	—	—

### Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name +A	BCR3PM-12LA
Lead form	Plastic Magazine (Tube)	50	Type name +A – Lead forming code	BCR3PM-12LA-A8

Note : Please confirm the specification about the shipping in detail.



# BCR3PM-12L

## Triac

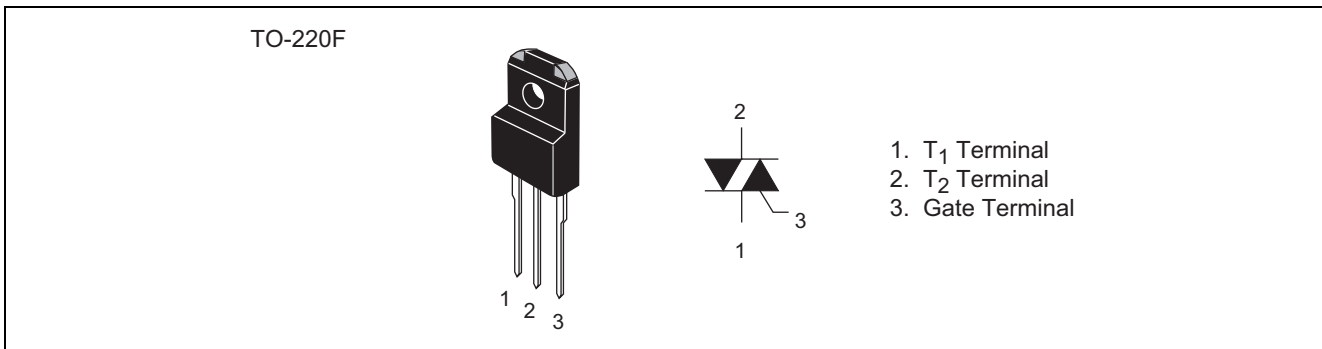
Low Power Use

(The product guaranteed maximum junction temperature of 150°C)

### Features

- $I_{T(RMS)}$  : 3 A
- $V_{DRM}$  : 600 V
- $I_{FGTI}, I_{RGTI}, I_{RGTIII}$  : 20 mA (10 mA)<sup>Note5</sup>
- Viso : 2000 V
- Insulated Type
- Planar Passivation Type

### Outline



### Applications

Contactless AC switch, light dimmer, electric blanket, control of household equipment such as electric fan, solenoid driver, small motor control, and other general purpose control applications

### Warning

1. Refer to the recommended circuit values around the triac before using.
2. Be sure to exchange the specification before using. Otherwise, general triacs with the maximum junction temperature of 125°C will be supplied.

### Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak off-state voltage <sup>Note1</sup>	$V_{DRM}$	600	V
Non-repetitive peak off-state voltage <sup>Note1</sup>	$V_{DSM}$	720	V

**BCR3PM-12L (The product guaranteed maximum junction temperature of 150°C)**

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_{T(RMS)}$	3.0	A	Commercial frequency, sine full wave 360° conduction, $T_c = 132^\circ\text{C}$
Surge on-state current	$I_{TSM}$	30	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
$I^2t$ for fusing	$I^2t$	3.7	$\text{A}^2\text{s}$	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	$P_{GM}$	3	W	
Average gate power dissipation	$P_{G(AV)}$	0.3	W	
Peak gate voltage	$V_{GM}$	6	V	
Peak gate current	$I_{GM}$	0.5	A	
Junction temperature	$T_j$	- 40 to +150	$^\circ\text{C}$	
Storage temperature	$T_{stg}$	- 40 to +150	$^\circ\text{C}$	
Mass	—	2.0	g	Typical value
Isolation voltage	Viso	2000	V	$T_a = 25^\circ\text{C}$ , AC 1 minute, $T_1 \cdot T_2 \cdot G$ terminal to case

Notes: 1. Gate open.

**Electrical Characteristics**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak off-state current	$I_{DRM}$	—	—	2.0	mA	$T_j = 150^\circ\text{C}$ , $V_{DRM}$ applied
On-state voltage	$V_{TM}$	—	—	1.5	V	$T_c = 25^\circ\text{C}$ , $I_{TM} = 4.5 \text{ A}$ , Instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	I	$V_{FGTI}$	—	—	1.5	$T_j = 25^\circ\text{C}$ , $V_D = 6 \text{ V}$ , $R_L = 6 \Omega$ , $R_G = 330 \Omega$
	II	$V_{RGTI}$	—	—	1.5	
	III	$V_{RGTIII}$	—	—	1.5	
Gate trigger current <sup>Note2</sup>	I	$I_{FGTI}$	—	—	20 <sup>Note5</sup>	$T_j = 25^\circ\text{C}$ , $V_D = 6 \text{ V}$ , $R_L = 6 \Omega$ , $R_G = 330 \Omega$
	II	$I_{RGTI}$	—	—	20 <sup>Note5</sup>	
	III	$I_{RGTIII}$	—	—	20 <sup>Note5</sup>	
Gate non-trigger voltage	$V_{GD}$	0.2/0.1	—	—	V	$T_j = 125^\circ\text{C}/150^\circ\text{C}$ , $V_D = 1/2 V_{DRM}$
Thermal resistance	$R_{th(j-c)}$	—	—	4.5	$^\circ\text{C}/\text{W}$	Junction to case <sup>Note3</sup>
Critical-rate of rise of off-state commutating voltage <sup>Note4</sup>	$(dv/dt)_c$	5/1	—	—	$\text{V}/\mu\text{s}$	$T_j = 125^\circ\text{C}/150^\circ\text{C}$

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. The contact thermal resistance  $R_{th(c-f)}$  in case of greasing is  $0.5^\circ\text{C}/\text{W}$ .

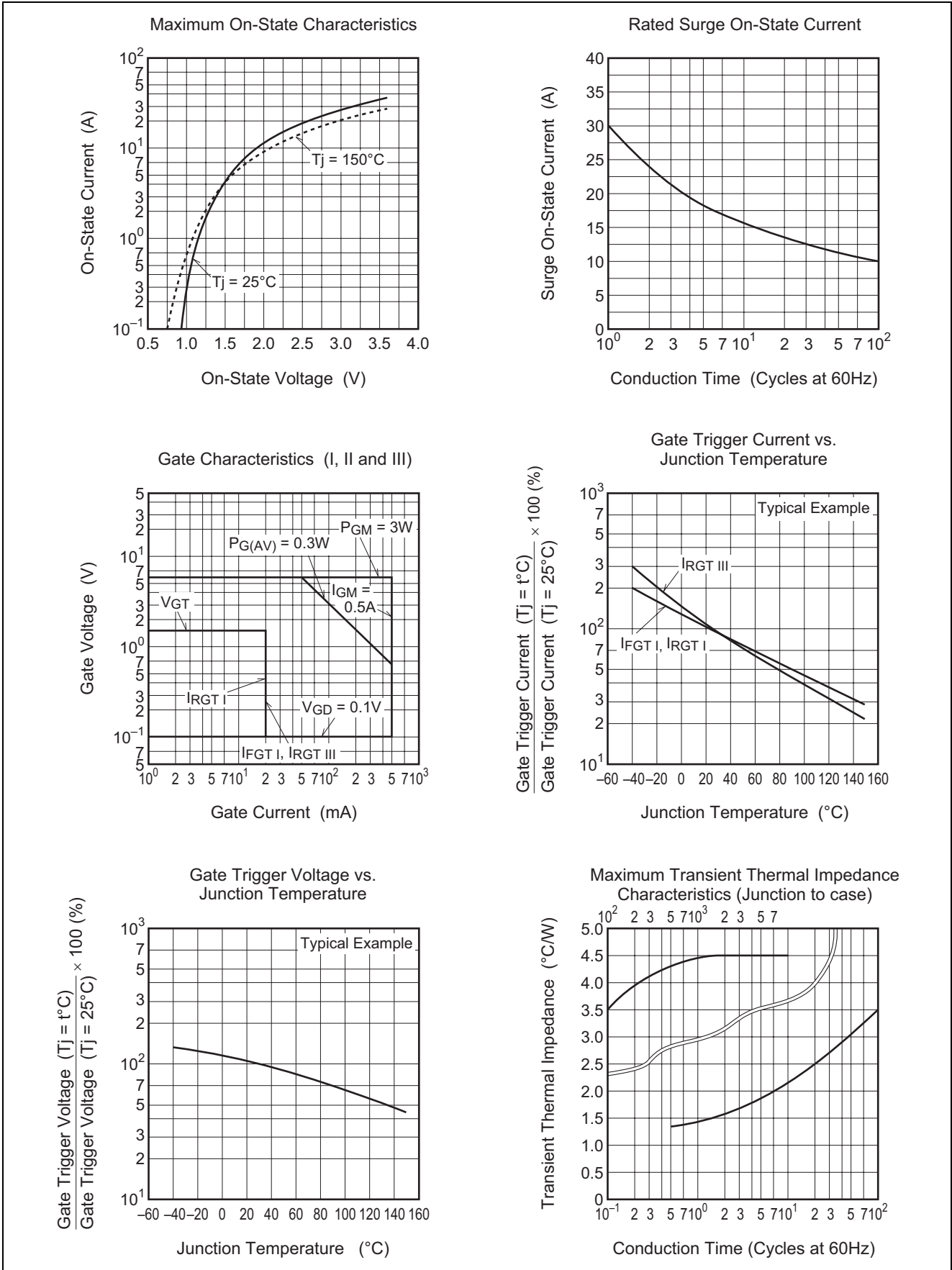
4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

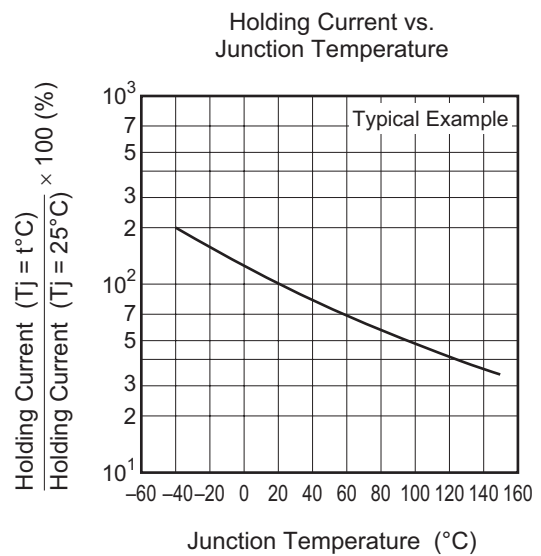
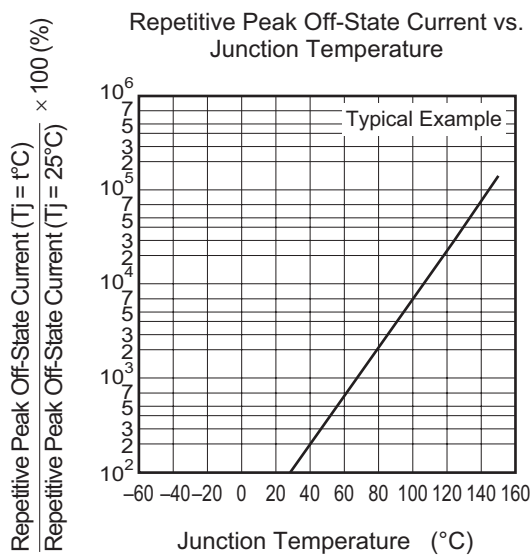
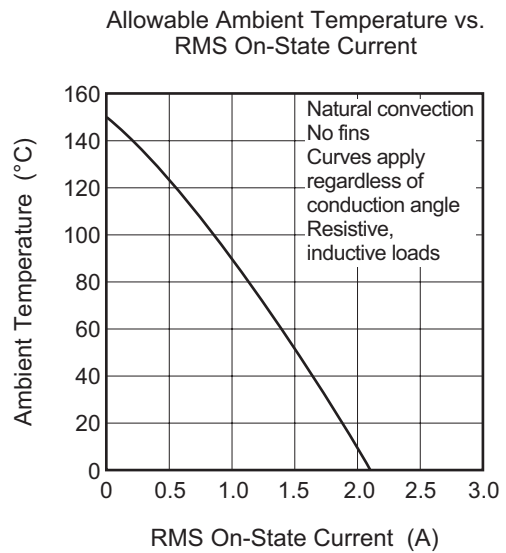
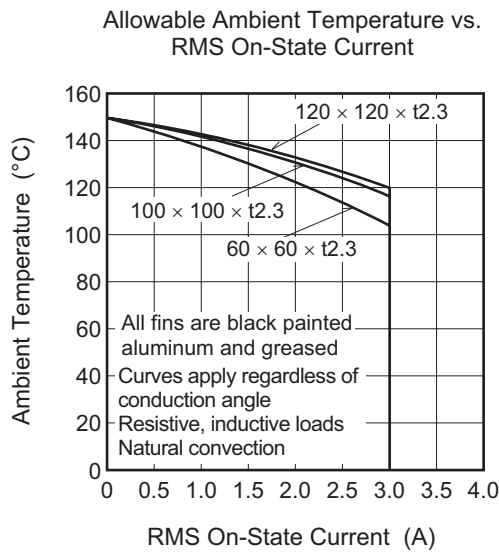
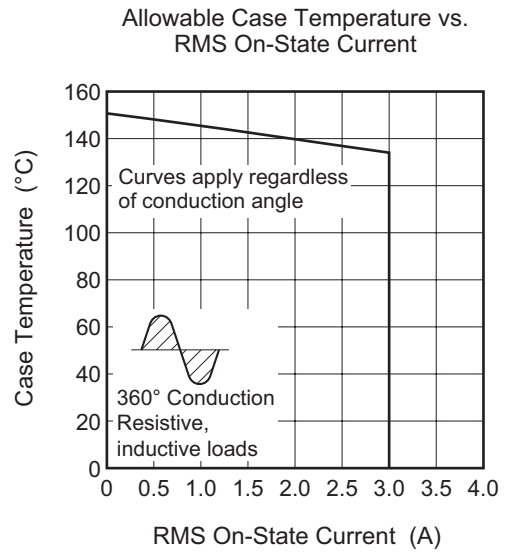
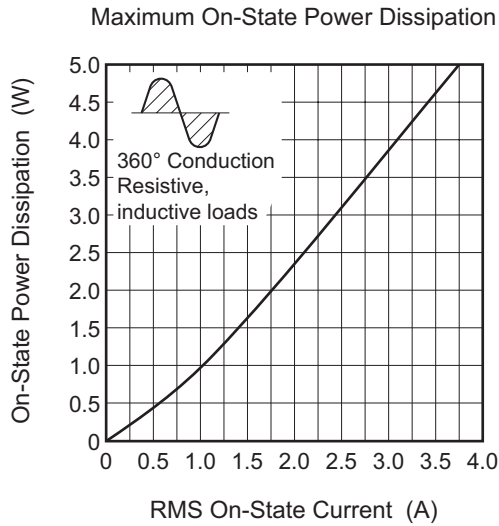
5. High sensitivity ( $I_{GT} \leq 10 \text{ mA}$ ) is also available. ( $I_{GT}$  item: 1)

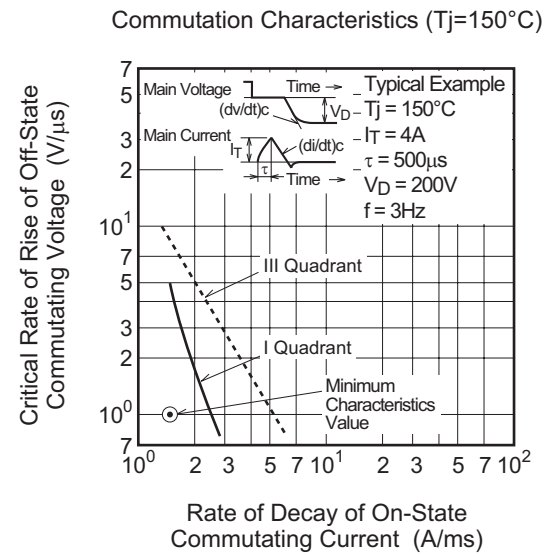
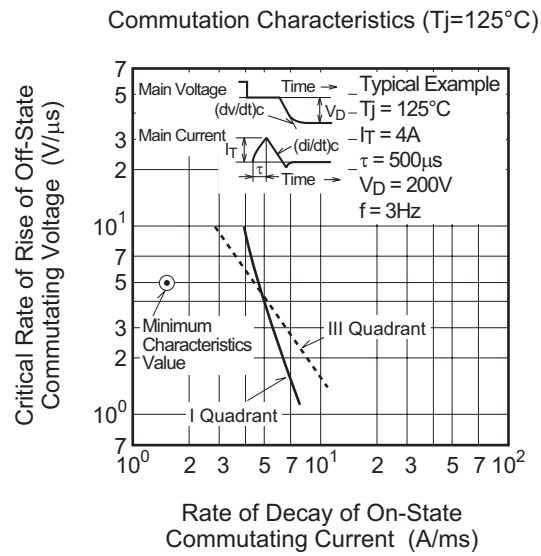
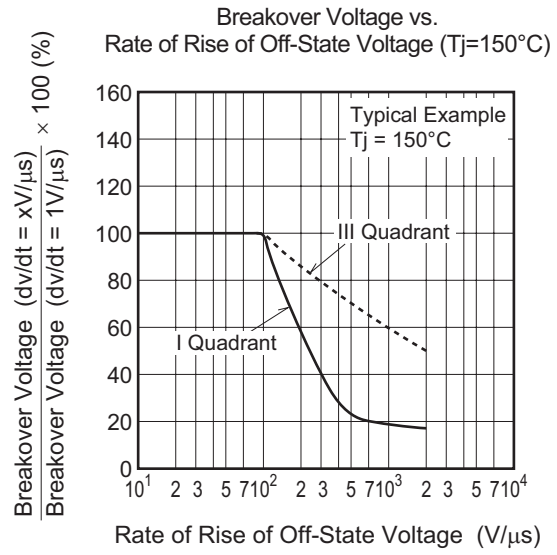
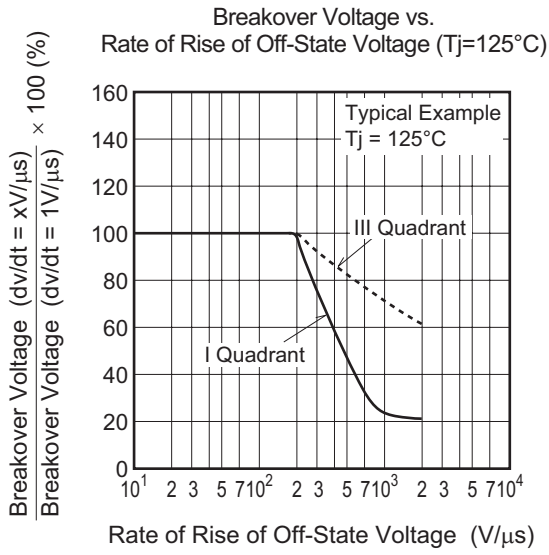
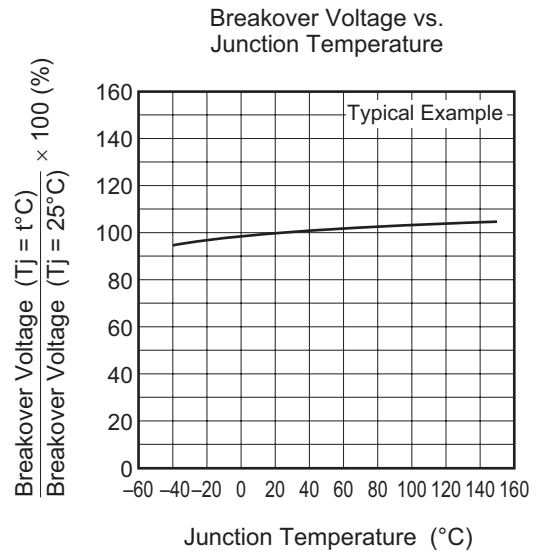
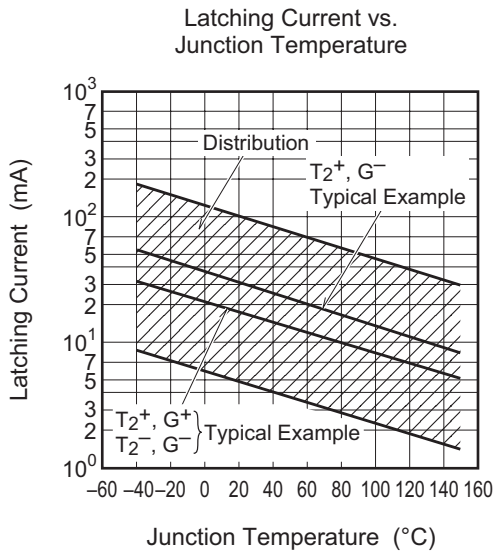
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature $T_j = 125^\circ\text{C}/150^\circ\text{C}$ 2. Rate of decay of on-state commutating current $(di/dt)_c = -1.5 \text{ A/ms}$ 3. Peak off-state voltage $V_D = 400 \text{ V}$	



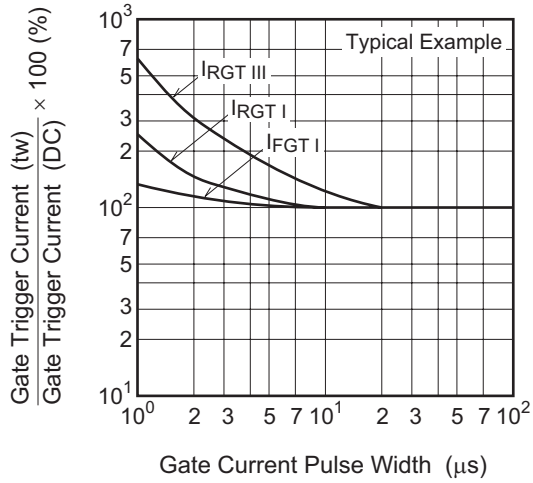
Performance Curves



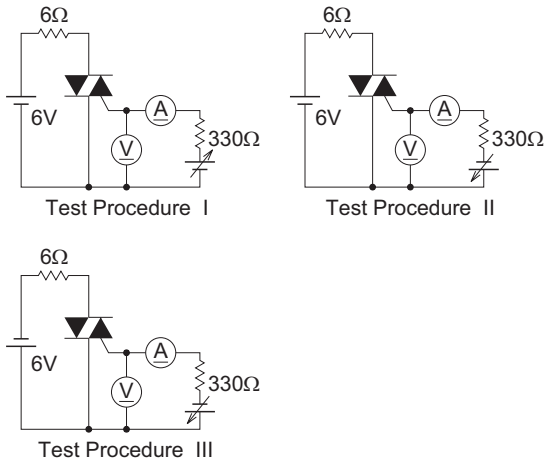




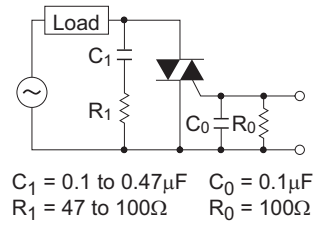
Gate Trigger Current vs. Gate Current Pulse Width



Gate Trigger Characteristics Test Circuits



Recommended Circuit Values Around The Triac



**Package Dimensions**

**TO-220F**

EIAJ Package Code	JEDEC Code	Mass (g) (reference value)	Lead Material
Conforms	—	2.0	Cu alloy

Symbol	Dimension in Millimeters		
	Min	Typ	Max
A	—	—	—
A <sub>1</sub>	—	—	—
A <sub>2</sub>	—	—	—
b	—	—	—
D	—	—	—
E	—	—	—
e	—	—	—
x	—	—	—
y	—	—	—
y <sub>1</sub>	—	—	—
ZD	—	—	—
ZE	—	—	—

Note 1) The dimensional figures indicate representative values unless otherwise the tolerance is specified.

**Order Code**

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name +B	BCR3PM-12LB
Lead form	Plastic Magazine (Tube)	50	Type name +B – Lead forming code	BCR3PM-12LB-A8

Note : Please confirm the specification about the shipping in detail.

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